



THE DATASHEET OF ZTX605STOA



ZTX604 ZTX605

NPN SILICON PLANAR MEDIUM POWER DARLINGTON TRANSISTOR

ISSUE 1 - MARCH 94

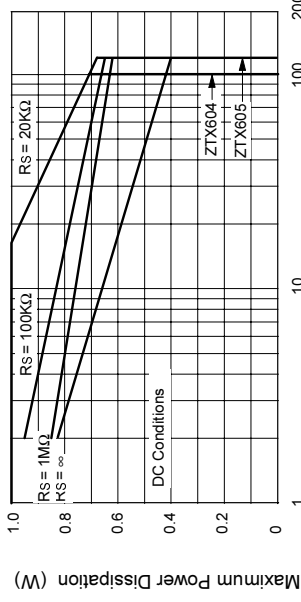
FEATURES

- * 120 Volt V_{CE0}
- * 1 Amp continuous current
- * Gain of 2K at $I_C=1$ Amp
- * $P_{tot}=1$ Watt

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	ZTX604		ZTX605		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Static Forward Current Transfer Ratio	h_{FE}	2K	100K	2K	100K		$I_C=50\text{mA}, V_{CE}=5\text{V}$
		5K		5K			$I_C=500\text{mA}, V_{CE}=5\text{V}^*$
		2K		2K			$I_C=1\text{A}, V_{CE}=5\text{V}^*$
		0.5K		0.5K			$I_C=2\text{A}, V_{CE}=5\text{V}^*$
Transition Frequency	f_T	150		150		MHz	$I_C=100\text{mA}, V_{CE}=10\text{V}$ $f=20\text{MHz}$
Input Capacitance	C_{ibo}	90 Typical				pF	$V_{EB}=500\text{mV}, f=1\text{MHz}$
Output Capacitance	C_{obo}	15 Typical				pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Switching Times	t_{on}	0.5 Typical				μs	$I_C=500\text{mA}, V_{CE}=10\text{V}$ $I_B=I_C=0.5\text{mA}$
	t_{off}	1.6 Typical				μs	

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$



VCE - Collector-Emitter Voltage (Volts)

Voltage Derating Graph

The maximum permissible operational temperature can be obtained from this graph using the following equation

$$T_{amb(max)} = \frac{Power(max) - Power(act)}{0.0057} + 25^\circ\text{C}$$

$T_{amb(max)}$ = Maximum operating ambient temperature

Power(max) = Maximum power dissipation figure, obtained from the above graph for a given VCE and source resistance (RS)

Power(actual) = Actual power dissipation in users circuit

ABSOLUTE MAXIMUM RATINGS

PARAMETER	MIN.	MAX.
Collector-Base Voltage		120
Collector-Emitter Voltage		100
Emitter-Base Voltage		10
Peak Pulse Current		
Continuous Collector Current		
Power Dissipation at $T_{amb}=25^\circ\text{C}$ derate above 25°C		

Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	Z
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	120
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	100
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	10
Collector Cut-Off Current	I_{CBO}	
Emitter Cut-Off Current	I_{EBO}	
Collector-Emitter Cut-Off Current	I_{CES}	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	

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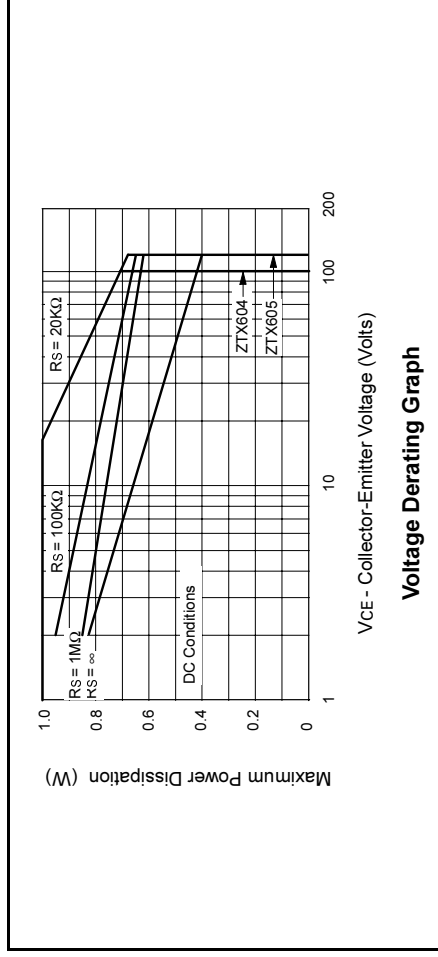
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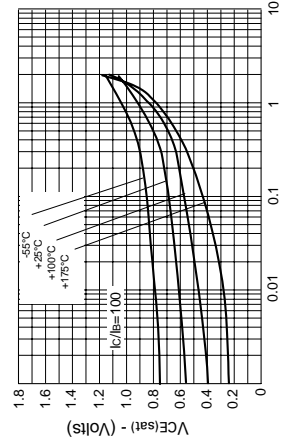
Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS

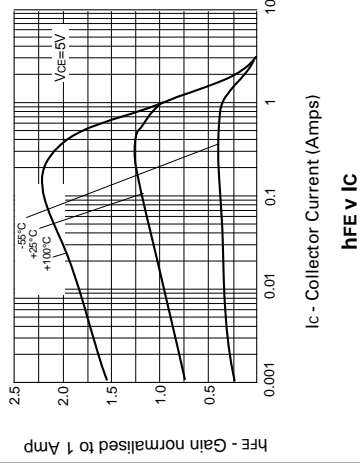
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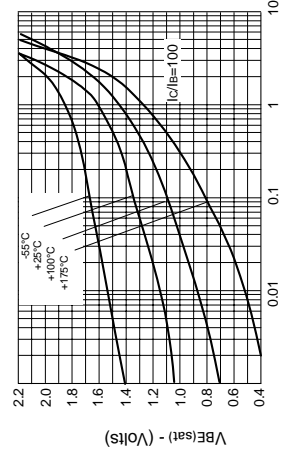
TYPICAL CHARACTERISTICS



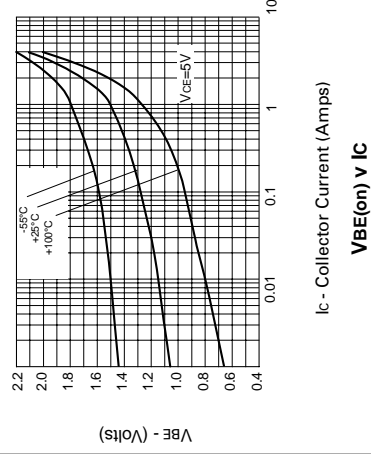
IC - Collector Current (Amps)
VCE(sat) v IC



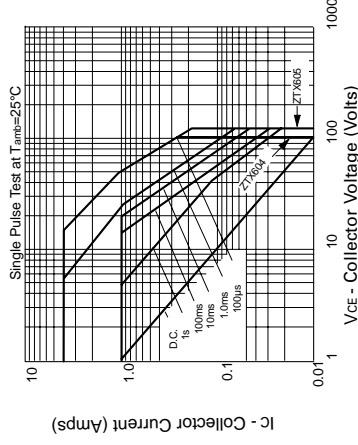
IC - Collector Current (Amps)
hFE v IC



IC - Collector Current (Amps)
VBE(sat) v IC



IC - Collector Current (Amps)
VBE(on) v IC



Safe Operating Area

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